

# Chris J Hodges

## List of Publications by Year in descending order

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15  
papers

187  
citations

1163117

8  
h-index

1281871

11  
g-index

15  
all docs

15  
docs citations

15  
times ranked

236  
citing authors

#	ARTICLE	IF	CITATIONS
1	Microwave-optical coupling via Rydberg excitons in cuprous oxide. Physical Review Research, 2022, 4, .	3.6	16
2	High-resolution nanosecond spectroscopy of even-parity Rydberg excitons in $\text{CuO}$ . Physical Review B, 2022, 105, .	3.2	11
3	Rydberg excitons in synthetic cuprous oxide $\text{CuO}$ . Physical Review Materials, 2021, 5, .	4.1	15
4	Giant Rydberg Excitons in Synthetic and Artificial Cuprous Oxide. , 2018, , .		0
5	Anomalous Green Luminescent Properties in CVD Synthetic Diamonds. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800292.	1.8	11
6	Solid state superatoms: Rydberg excitons in cuprous oxide. , 2017, , .		0
7	Monitoring the photocatalytic oxidation of water-based organic pollutants by FT-IR spectroscopy in real-time. , 2016, , .		0
8	Mechanism of hot electron electroluminescence in GaN-based transistors. Journal Physics D: Applied Physics, 2016, 49, 435101.	2.8	20
9	Mid-infrared spectroscopy of sulphur and selenium donors in silicon for quantum optics. , 2016, , .		0
10	Probing temperature gradients within the GaN buffer layer of AlGaIn/GaN high electron mobility transistors with Raman thermography. Journal of Applied Physics, 2014, 115, .	2.5	10
11	Liquid crystal electrography: Electric field mapping and detection of peak electric field strength in AlGaIn/GaN high electron mobility transistors. Microelectronics Reliability, 2014, 54, 921-925.	1.7	3
12	AlGaIn/GaN field effect transistors for power electronicsâ€™ Effect of finite GaN layer thickness on thermal characteristics. Applied Physics Letters, 2013, 103, .	3.3	18
13	Analysis of strained surface layers of ZnO single crystals after irradiation with intense femtosecond laser pulses. Applied Physics Letters, 2013, 102, .	3.3	2
14	On the link between electroluminescence, gate current leakage, and surface defects in AlGaIn/GaN high electron mobility transistors upon off-state stress. Applied Physics Letters, 2012, 101, .	3.3	54
15	Optical investigation of degradation mechanisms in AlGaIn/GaN high electron mobility transistors: Generation of non-radiative recombination centers. Applied Physics Letters, 2012, 100, .	3.3	31